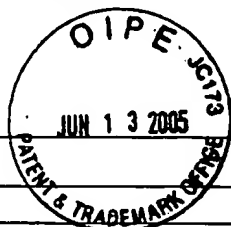


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Application Number	09/945,535
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First Named Inventor	Ahn, Kie
Group Art Unit	2813
Examiner Name	Blum, David

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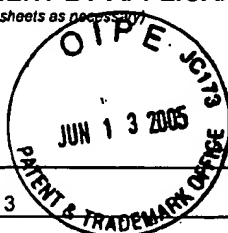
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Group Art Unit 2813
Examiner Name Blum, David

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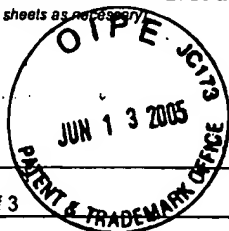
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Group Art Unit	2813
Examiner Name	Blum, David

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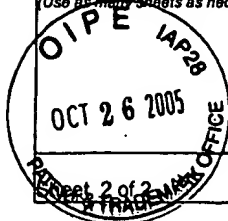
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